<u>Standard specifications of</u> 100 mm β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

Items	Specifications	
Dopant	Si (n-type)	β -Ga ₂ O ₃ epitaxial layer
Doping concentration *A value can be selected in increments of 1×10^{16} cm ⁻³ .	Specify a value in the range between 1×10 ¹⁶ and 9×10 ¹⁶ cm ⁻³	β-Ga ₂ O ₃ wafer Cross section of β-Ga ₂ O ₃
Thickness *A value can be selected in increments 1 µm.	Specify a value in the range between 5 and 10 µm	epitaxial wafer
Epi-Wafer		
Items	Specifications	
Substrate dopant	Sn (n-type)	IF (001)
Substrate resistivity	0.007–0.042 Ω · cm	
Surface orientation	(001)	
Backside finish	Grinding	OF [100]
Wafer thickness	620 µm	Orientation
XRD FWHM *Not included in a delivery inspection she	≤50 arcsec	
Remarks 1 There are cases in which the other side of OF	is chipped (a maximum of around IF width).	

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1 There are cases in which the other side of OF is chipped (a maximum of around IF width).

2 These products must be used for research and development purposes only.

3 The substrates must not be used as a seed crystal.

4 The specifications are subject to change without notice.

<u>Standard specifications of</u> 2 inch β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

Items	Specifications	
Dopant	Si (n-type)	β -Ga ₂ O ₃ epitaxial layer
Doping concentration *A value can be selected in increments of 1×10^{16} cm ⁻³ .	Specify a value in the range between 1×10 ¹⁶ and 9×10 ¹⁶ cm ⁻³	β-Ga ₂ O ₃ wafer Cross section of β-Ga ₂ O ₃
Thickness *A value can be selected in increments 1 µm.	Specify a value in the range between 5 and 10 µm	epitaxial wafer
Epi-Wafer		
Items	Specifications	
Substrate dopant	Sn (n-type)	IF (001)
Substrate resistivity	0.007–0.042 Ω · cm	
Surface orientation	(001)	
Backside finish	Grinding	OF [100]
Wafer thickness	640 µm	Orientation
XRD FWHM *Not included in a delivery inspection she	≤50 arcsec	
Remarks 1 There are cases in which the other side of OF	is chipped (a maximum of around IF width).	

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